

RJK5009DPP

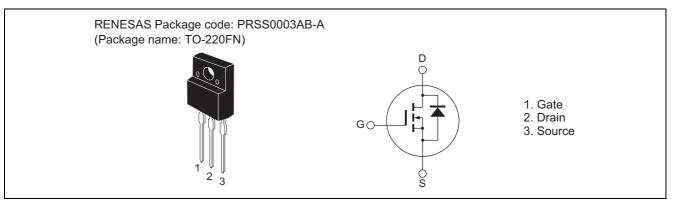
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1606-0100 Rev.1.00 Dec 04, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Item Symbol		Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID Note4	20	А
Drain peak current	I _{D (pulse)} Note1	60	А
Body-drain diode reverse drain current	I _{DR}	20	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	60	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.88	mJ
Channel dissipation	Pch Note2	40	W
Channel to case thermal impedance	θch-c	3.125	°C/W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

4. Limited by maximum safe operation area

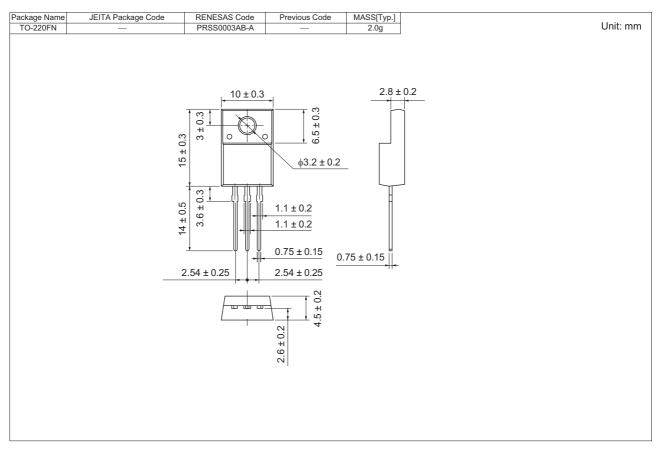
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500	—		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	—	—	1	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	V_{GS} = ±30 V, V_{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	—	0.260	0.325	Ω	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss		2100	_	pF	V _{DS} = 25 V
Output capacitance	Coss		220		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		27		pF	
Turn-on delay time	t _{d(on)}		35		ns	I _D = 10 A
Rise time	tr	_	33		ns	$V_{GS} = 10 V$ $R_L = 25 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	97		ns	
Fall time	t _f	_	17		ns	
Total gate charge	Qg	_	52		nC	$V_{DD} = 400 V$ $V_{GS} = 10 V$ $I_D = 20 A$
Gate to source charge	Qgs	_	10.5		nC	
Gate to drain charge	Qgd	_	22		nC	
Body-drain diode forward voltage	V _{DF}	_	1.0	1.6	V	$I_F = 20 \text{ A}, V_{GS} = 0^{Note5}$
Body-drain diode reverse recovery time	t _{rr}		320	—	ns	$I_F = 20 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
RJK5009DPP-00-T2	1050 pcs	Box (Tube)

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